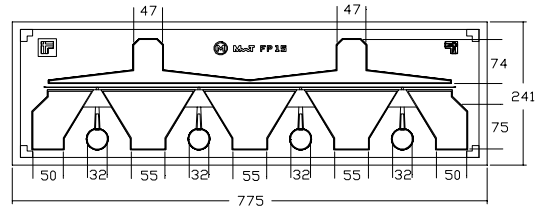


Features:

- +28.5 dBm Output Power at 12 GHz
- 12 dB Small Signal Gain at 12 GHz
- 60% PAE at 12 GHz
- 0.3 x 630 Micron Refractory Metal/Gold Gate
- Excellent for High Power, Gain, and High Power Added Efficiency up to 28 GHz
- Ideal for Commercial, Military, Hi-Rel Space Applications



Chip Dimensions: 775 x 241 microns
Chip Thickness: 100 microns

Description:

The MwT-PH15 is a AlGaAs/InGaAs PHEMT (Pseudomorphic-High-Electron-Mobility-Transistor) device whose nominal 0.3 micron gate length and 630 micron gate width make it ideally suited for applications requiring high-gain and power up to 28 GHz frequency range with power outputs ranging from 500 to 700 milli-watts. The device is equally effective for either wideband (e.g. 6 to 18 GHz) or narrow-band applications. The chip is produced using MwT's reliable metal systems and all devices from each wafer are screened to insure reliability. All chips are passivated using MwT's patented "Diamond-Like Carbon" process for increased durability.

Electrical Specifications:

• at $T_a = 25\text{ }^\circ\text{C}$

SYMBOL	PARAMETERS & CONDITIONS	FREQ	UNITS	MIN	TYP
P1dB	Output Power at 1dB Compression Vds=7.0 V Ids=0.75xIDSS=150 mA	12 GHz	dBm	27.0	28.5
		18 GHz			28.5
SSG	Small Signal Gain Vds=7.0 V Ids=0.75xIDSS=150 mA	12 GHz	dB	10.0	12.0
		18 GHz			9.5
PAE	Power Added Efficiency at P1dB Vds=7.0 V Ids=0.75xIDSS=150 mA	12 GHz	%		60
IDSS	Recommended IDSS Range for Optimum P1dB		mA		140 - 220

DC Specifications:

• at $T_a = 25\text{ }^\circ\text{C}$

SYMBOL	PARAMETERS & CONDITIONS	UNITS	MIN	TYP	MAX
IDSS	Saturated Drain Current Vds=4.0 V Vgs=0.0 V	mA	120		240
Gm	Transconductance Vds=2.5 V Vgs=0.0 V	mS	130	200	
Vp	Pinch-off Voltage Vds=3.0 V Ids=2.0 mA	V		-1.2	-2.5
BVGSO	Gate-to-Source Breakdown Voltage Igs= -0.7 mA	V	-6.0	-10.0	

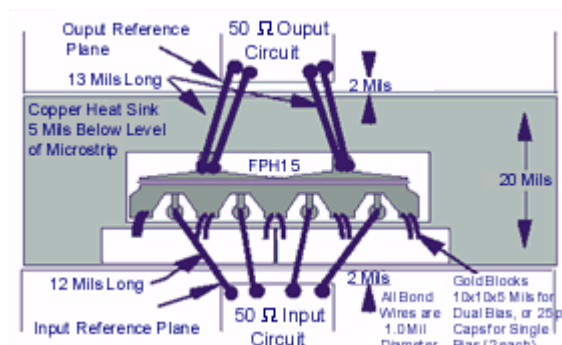
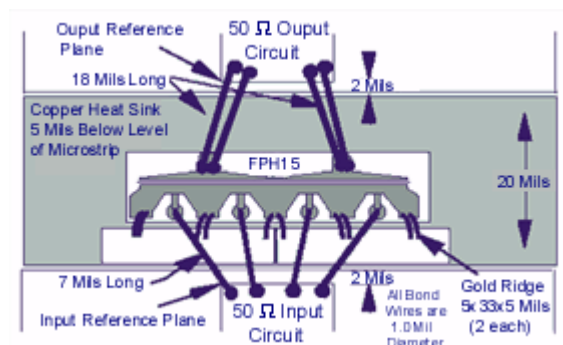
BVGO	Gate-to-Drain Breakdown Voltage Igd= -0.7 mA	V	-10.0	-13.0
Rth	Chip Thermal Resistance	C/W		65*

* Overall Rth depends on case mounting

DEVICE EQUIVALENT CIRCUIT	PARAMETER	VALUE
	Source Resistance	Rs 0.10 ohm
	Source Inductance	Ls 0.03 nH
	Drain-Source Resistance	Rds 200 ohm
	Drain-Source Capacitance	Cds 0.12 pF
	Drain Resistance	Rd 0.84 ohm
	Drain Pad Capacitance	Cpd 0.05 pF
	Drain Inductance	Ld 0.10 nH
	Gate Bond Wire Inductance	Lg 0.07 nH
	Gate Pad Capacitance	Cpg 0.20 pF
	Gate Resistance	Rg 0.10 ohm
	Gate-Source Capacitance	Cgs 1.30 pF
	Channel Resistance	Ri 2.30 ohm
	Gate-Drain Capacitance	Cgd 0.07 pF
	Transconductance	gm 200 mS
	Transit Time	tau 2.60 psec

MwT-PH15 DUAL BIAS

MwT-PH15 SELF BIAS



MAXIMUM RATINGS AT Ta = 25 °C

Symbol	Parameter	Units	Cont Max1	Absolute Max2
VDS	Drain to Source Volt.	V	7.5	8.0
Tch	Channel Temperature	°C	+150	+175



MwT-PH15

28 GHz Medium Power AlGaAs/InGaAs PHEMT

May 2011

Tst	Storage Temperature	°C	-65 to+150	+175
Pin	RF Input Power	mW	200	300
Pt	Total Power Dissipation	mW	1900	2300

Notes:

1. Exceeding any one of these limits in continuous operation may reduce the mean-time- to-failure below the design goal.
2. Exceeding any one of these limits may cause permanent damage.